



PSMN2R6-60PSQ Information



For Reference Only

Part Number PSMN2R6-60PSQ Manufacturer Nexperia USA Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 150A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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PSMN2R6-60PSQ Specifications

Manufacturer Part Number PSMN2R6-60PSQ Manufacturer Nexperia USA Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 150A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ ImA Gate Charge (Qg) (Max) @ Vgs 140nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7629pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 326W (Tc) Rds On (Max) @ Id, Vgs 2.6 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) four - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) #20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Jenuman Salew (Tc) Supplier Device Package Package / Case TO-220AB Package / Case	Manufacturer Part Number	PSMN2R6-60PSQ
Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 150A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ ImA Gate Charge (Qg) (Max) @ Vgs 140nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7629pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 326W (Tc) Rds On (Max) @ Id, Vgs 2.6 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Manufacturer	Nexperia USA Inc.
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C150A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 1mAGate Charge (Qg) (Max) @ Vgs140nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7629pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)326W (Tc)Rds On (Max) @ Id, Vgs2.6 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case MOSFET (Metal Oxide) 60V MOSFET (Metal Oxide) 60V 60V 60V 150A (Tc) 150A (Tc) 150A (Tc) 160A 4V @ 1mA 4V @ 10V 140C @ 10V 7629pF @ 25V 25V 25V 26W (Tc) 26 mOhm @ 25A, 10V 70-220AB 70-220AB	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C150A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 1mAGate Charge (Qg) (Max) @ Vgs140nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7629pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)326W (Tc)Rds On (Max) @ Id, Vgs2.6 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 150A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 140nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7629pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) 326W (Tc) Rds On (Max) @ Id, Vgs 2.6 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220AB	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 140nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7629pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 326W (Tc) Rds On (Max) @ Id, Vgs 2.6 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 140nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7629pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 326W (Tc) Rds On (Max) @ Id, Vgs 2.6 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	150A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 7629pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2.6 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 7629pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2.6 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)326W (Tc)Rds On (Max) @ Id, Vgs2.6 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	140nC @ 10V
FET Feature - Power Dissipation (Max) 326W (Tc) Rds On (Max) @ Id, Vgs 2.6 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	7629pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2.6 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs2.6 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	326W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	2.6 mOhm @ 25A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
•		Report errors?

PSMN2R6-60PSQ Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

PSMN2R6-60PSQ Payment Methods



















PSMN2R6-60PSQ Shipping Methods













If you have any question about PSMN2R6-60PSQ, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com